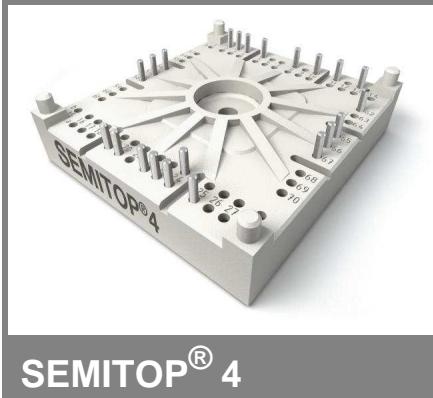


# SK50GD126T



## IGBT Module

**SK50GD126T**

Preliminary Data

### Features

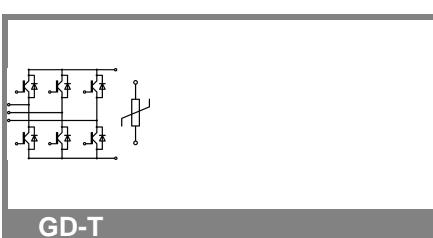
- One screw mounting module
- Fully compatible with SEMITOP®1,2,3
- Improved thermal performances by aluminium oxide substrate
- Trench IGBT technology
- CAL technology FWD
- Integrated NTC temperature sensor

### Typical Applications\*

- Inverter up to 28 kVA
- Typ. motor power 15 kW

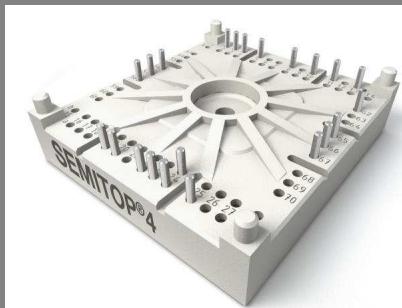
Absolute Maximum Ratings		$T_s = 25^\circ\text{C}$ , unless otherwise specified		
Symbol	Conditions	Values		Units
<b>IGBT</b>				
$V_{CES}$	$T_j = 25^\circ\text{C}$	1200		V
$I_C$	$T_j = 150^\circ\text{C}$ $T_s = 25^\circ\text{C}$ $T_s = 70^\circ\text{C}$	68 52	A A	
$I_{CRM}$	$I_{CRM} = 2 \times I_{Cnom}$	100		A
$V_{GES}$		$\pm 20$		V
$t_{psc}$	$V_{CC} = 600\text{ V}; V_{GE} \leq 20\text{ V}; T_j = 125^\circ\text{C}$ $V_{CES} < 1200\text{ V}$	10		$\mu\text{s}$
<b>Inverse Diode</b>				
$I_F$	$T_j = 150^\circ\text{C}$ $T_s = 25^\circ\text{C}$ $T_s = 70^\circ\text{C}$	62 46	A A	
$I_{FRM}$	$I_{FRM} = 2 \times I_{Fnom}$	100		A
<b>Module</b>				
$I_t(\text{RMS})$				A
$T_{vj}$		-40 ... +150		$^\circ\text{C}$
$T_{stg}$		-40 ... +125		$^\circ\text{C}$
$V_{isol}$	AC, 1 min.	2500		V

Characteristics		$T_s = 25^\circ\text{C}$ , unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	
<b>IGBT</b>					
$V_{GE(\text{th})}$	$V_{GE} = V_{CE}, I_C = 2\text{ mA}$	5	5,8	6,5	V
$I_{CES}$	$V_{GE} = 0\text{ V}, V_{CE} = V_{CES}$ $T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$			0,0067	mA
$I_{GES}$	$V_{CE} = 0\text{ V}, V_{GE} = 20\text{ V}$ $T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$			600	nA
$V_{CE0}$		1	1,2		V
	$T_j = 25^\circ\text{C}$		0,9	1,1	V
$T_j = 125^\circ\text{C}$					
$r_{CE}$	$V_{GE} = 15\text{ V}$ $T_j = 25^\circ\text{C}$ $T_j = 125^\circ\text{C}$	14	19		$\text{m}\Omega$
		22	27		$\text{m}\Omega$
$V_{CE(\text{sat})}$	$I_{Cnom} = 50\text{ A}, V_{GE} = 15\text{ V}$ $T_j = 25^\circ\text{C}_{\text{chilev.}}$ $T_j = 125^\circ\text{C}_{\text{chilev.}}$	1,7	2,1		V
		2	2,45		V
$C_{ies}$		3,6			nF
$C_{oes}$		0,188			nF
$C_{res}$		0,163			nF
$t_{d(on)}$		115			ns
$t_r$		28			ns
$E_{on}$		4,6			mJ
$t_{d(off)}$	$R_{Gon} = 8\text{ }\Omega$	509			ns
$t_f$		100			ns
$E_{off}$		6,3			mJ
$R_{th(j-s)}$	per IGBT	0,6			K/W



**GD-T**

# SK50GD126T



SEMITOP® 4

## IGBT Module

### SK50GD126T

Preliminary Data

## Features

- One screw mounting module
- Fully compatible with SEMITOP®1,2,3
- Improved thermal performances by aluminium oxide substrate
- Trench IGBT technology
- CAL technology FWD
- Integrated NTC temperature sensor

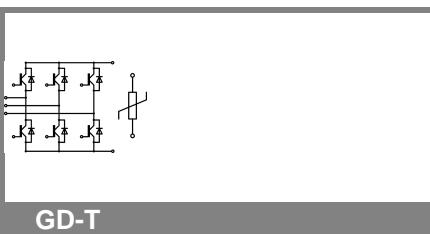
## Typical Applications\*

- Inverter up to 28 kVA
- Typ. motor power 15 kW

Characteristics		min.	typ.	max.	Units
Symbol	Conditions				
<b>Inverse Diode</b>					
$V_F = V_{EC}$	$I_{Fnom} = 50 \text{ A}; V_{GE} = 0 \text{ V}$ $T_j = 25 \text{ }^\circ\text{C}_{\text{chilev.}}$ $T_j = 125 \text{ }^\circ\text{C}_{\text{chilev.}}$		1,35		V
$V_{FO}$	$T_j = 25 \text{ }^\circ\text{C}$ $T_j = 125 \text{ }^\circ\text{C}$		0,95		V
$r_F$	$T_j = 25 \text{ }^\circ\text{C}$ $T_j = 125 \text{ }^\circ\text{C}$		8		$\text{m}\Omega$
$I_{RRM}$	$I_F = 50 \text{ A}$ $Q_{rr}$	$T_j = 125 \text{ }^\circ\text{C}$	30		A
$E_{rr}$	$dI/dt = 500 \text{ A}/\mu\text{s}$		10		$\mu\text{C}$
	$V_{CC} = 600 \text{ V}$		3,6		$\text{mJ}$
$R_{th(j-s)D}$	per diode		1		K/W
$M_s$	to heat sink	2,5	2,75		Nm
w			60		g
<b>Temperature sensor</b>					
$R_{100}$	$T_s = 100 \text{ }^\circ\text{C} (R_{25}=5\text{k}\Omega)$		493±5%		$\Omega$

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

\* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.



# SK50GD126T

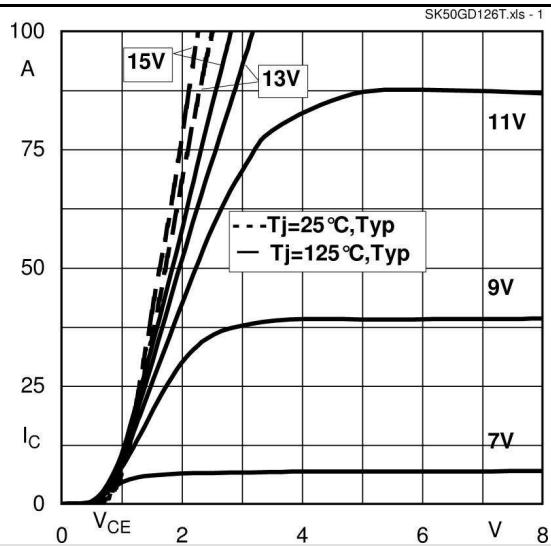


Fig. 1 Typ. output characteristic, inclusive  $R_{CC} + EE'$

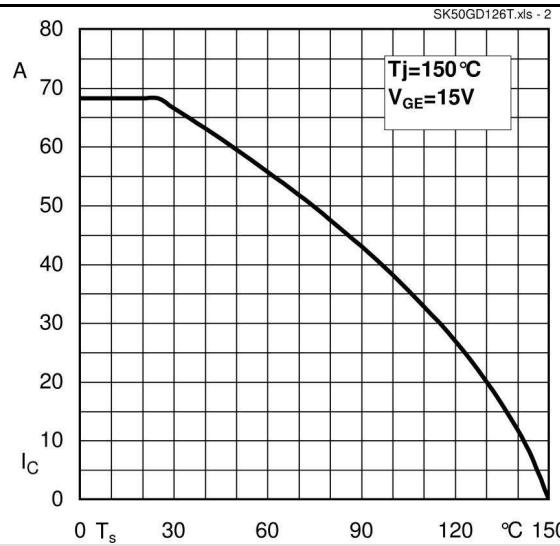


Fig. 2 Rated current vs. temperature  $I_C = f (T_s)$

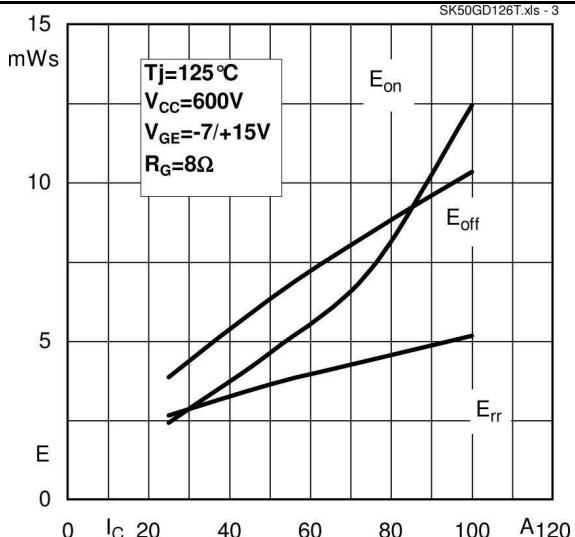


Fig. 3 Typ. turn-on /-off energy = f ( $I_C$ )

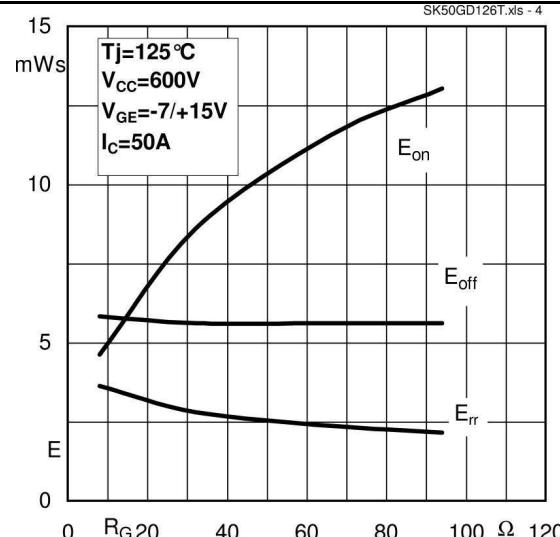


Fig. 4 Typ. turn-on /-off energy = f ( $R_G$ )

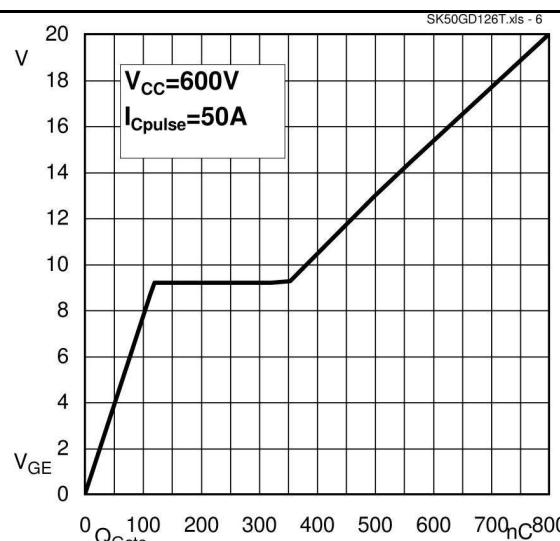


Fig. 6 Typ. gate charge characteristic

# SK50GD126T

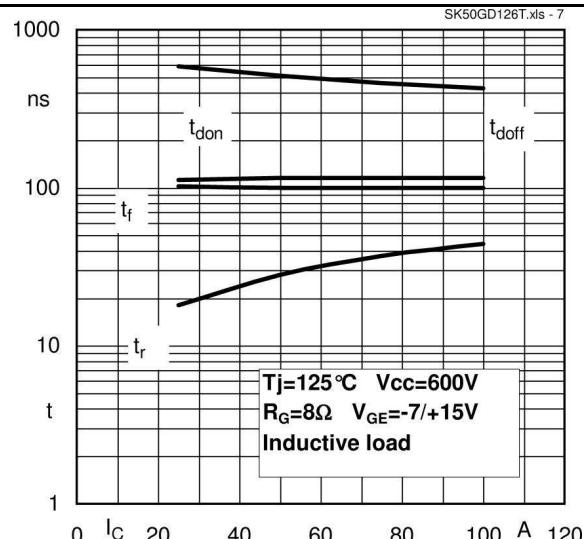


Fig. 7 Typ. switching times vs.  $I_c$

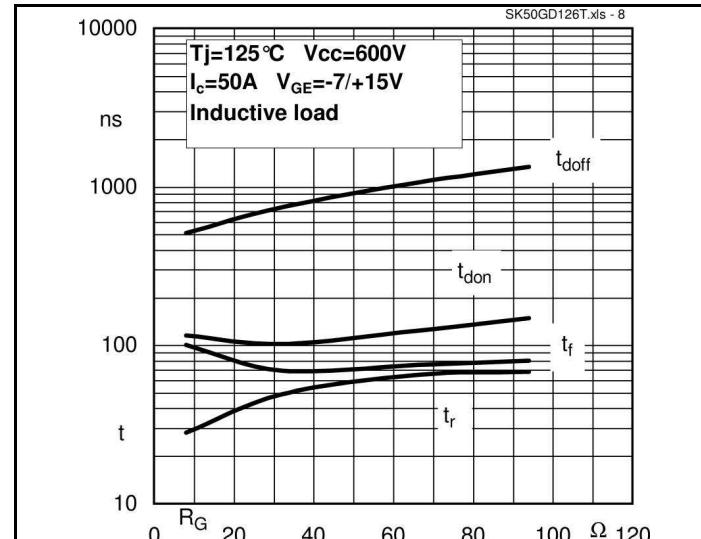


Fig. 8 Typ. switching times vs. gate resistor  $R_G$

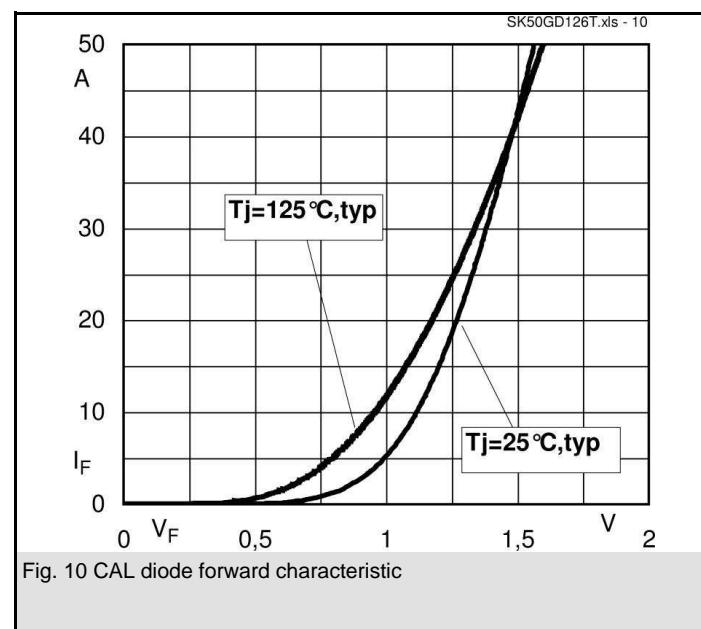
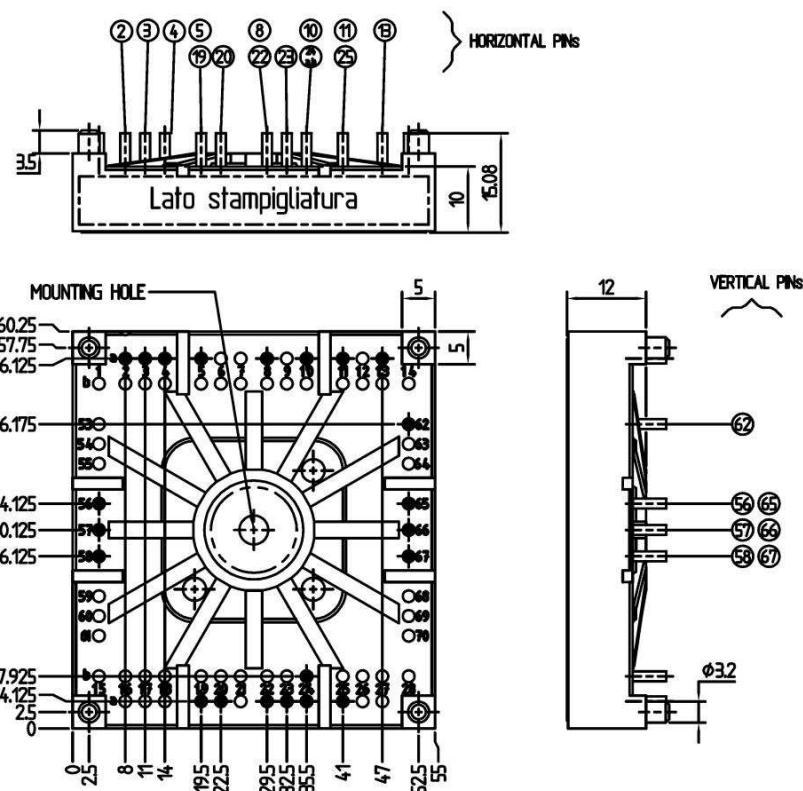


Fig. 10 CAL diode forward characteristic

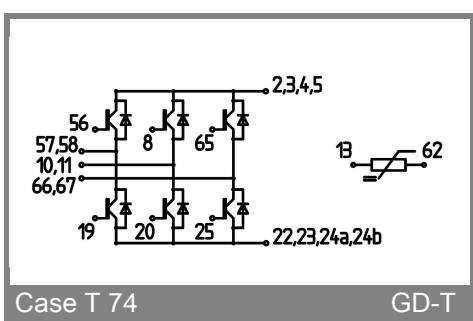
# SK50GD126T

UL recognized file

no. E 63 532



Case T74 (Suggested hole diameter for the solder pins in the circuit board: 2mm. Suggested hole diameter for the mounting pins in the circuit board: 3,6mm )



Case T 74

GD-T